

ABSTRACT OF THE DISCLOSURE

A light is irradiated on a wafer including a plurality of pixels. Image information corresponding to each pixel is measured by sensing the light reflected by the wafer surface. A raw datum is calculated by subtracting the image information of a corresponding pixel from the image information of a target pixel. The target pixel is a subject pixel for detecting a defect. The corresponding pixel is a pixel located in a first device unit and corresponds to the target pixel. The first device unit is located adjacent to a second device unit that includes the target pixel. The threshold region is preset to have at least one pair of upper and lower limits. The target pixel is marked as a defective pixel when the raw datum thereof is included in the threshold region. Accordingly, the killer defect can be detected separate from the non-killer defects that are usually detected together with the killer defects.